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IGBT

SGH80N60UFD

Ultrafast IGBT
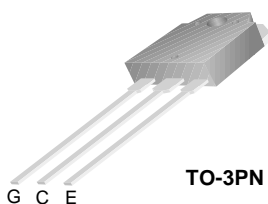
General Description

Fairchild's UFD series of Insulated Gate Bipolar Transistors (IGBTs) provides low conduction and switching losses. The UFD series is designed for applications such as motor control and general inverters where high speed switching is a required feature.
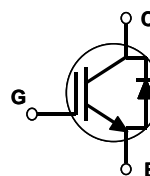
Features

- High speed switching
- Low saturation voltage : $V_{CE(sat)}$ = 2.1 V @ I_C = 40A
- High input impedance
- CO-PAK, IGBT with FRD : t_{rr} = 50ns (typ.)

Applications

AC & DC motor controls, general purpose inverters, robotics, and servo controls.

TO-3PN

G C E

Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Description		SGH80N60UFD	Units
V_{CES}	Collector-Emitter Voltage		600	V
V_{GES}	Gate-Emitter Voltage		± 20	V
I_C	Collector Current	@ T_C = 25°C	80	A
	Collector Current	@ T_C = 100°C	40	A
$I_{CM\,(1)}$	Pulsed Collector Current		220	A
I_F	Diode Continuous Forward Current	@ T_C = 100°C	25	A
I_{FM}	Diode Maximum Forward Current		280	A
P_D	Maximum Power Dissipation	@ T_C = 25°C	195	W
	Maximum Power Dissipation	@ T_C = 100°C	78	W
T_J	Operating Junction Temperature		-55 to +150	°C
T_{stg}	Storage Temperature Range		-55 to +150	°C
T_L	Maximum Lead Temp. for Soldering Purposes,/8" from Case for 5 Seconds		300	°C

Notes :
(1) Repetitive rating : Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$(IGBT)	Thermal Resistance, Junction-to-Case	--	0.64	°C/W
$R_{\theta JC}$(DIODE)	Thermal Resistance, Junction-to-Case	--	0.83	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	°C/W

Electrical Characteristics of the IGBT $T_C = 25°C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{CES}	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 250uA$	600	--	--	V
$\Delta B_{VCES}/\Delta T_J$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0V, I_C = 1mA$	--	0.6	--	V/°C
I_{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$	--	--	250	uA
I_{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$	--	--	± 100	nA
On Characteristics						
$V_{GE(th)}$	G-E Threshold Voltage	$I_C = 40mA, V_{CE} = V_{GE}$	3.5	4.5	6.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 40A, \quad V_{GE} = 15V$	--	2.1	2.6	V
		$I_C = 80A, \quad V_{GE} = 15V$	--	2.6	--	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	$V_{CE} = 30V, V_{GE} = 0V,$ f = 1MHz	--	2790	--	pF
C_{oes}	Output Capacitance		--	350	--	pF
C_{res}	Reverse Transfer Capacitance		--	100	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 300$ V, $I_C = 40A,$ $R_G = 5\Omega, V_{GE} = 15V,$ Inductive Load, $T_C = 25°C$	--	23	--	ns
t_r	Rise Time		--	50	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	90	130	ns
t_f	Fall Time		--	50	150	ns
E_{on}	Turn-On Switching Loss		--	570	--	uJ
E_{off}	Turn-Off Switching Loss		--	590	--	uJ
E_{ts}	Total Switching Loss		--	1160	1500	uJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 300$ V, $I_C = 40A,$ $R_G = 5\Omega, V_{GE} = 15V,$ Inductive Load, $T_C = 125°C$	--	30	--	ns
t_r	Rise Time		--	55	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	150	200	ns
t_f	Fall Time		--	160	250	ns
E_{on}	Turn-On Switching Loss		--	630	--	uJ
E_{off}	Turn-Off Switching Loss		--	940	--	uJ
E_{ts}	Total Switching Loss		--	1580	2000	uJ
Q_g	Total Gate Charge	$V_{CE} = 300$ V, $I_C = 40A,$ $V_{GE} = 15V$	--	175	250	nC
Q_{ge}	Gate-Emitter Charge		--	25	40	nC
Q_{gc}	Gate-Collector Charge		--	60	90	nC
L_e	Internal Emitter Inductance	Measured 5mm from PKG	--	14	--	nH

Electrical Characteristics of DIODE $T_C = 25°C$ unless otherwise noted

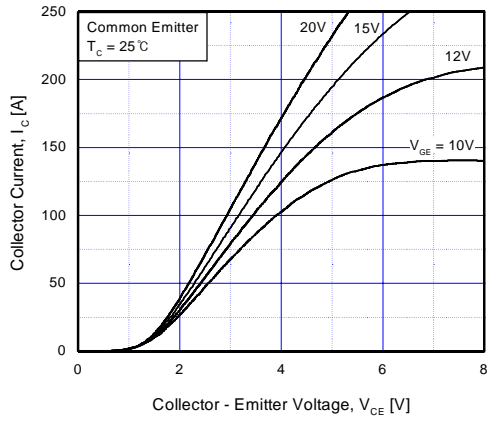| Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Units
V_{FM}	Diode Forward Voltage	$I_F = 25A$	$T_C = 25°C$	--	1.4	1.7	V
			$T_C = 100°C$	--	1.3	--	
t_{rr}	Diode Reverse Recovery Time	$I_F = 25A,$ di/dt = 200A/us	$T_C = 25°C$	--	50	95	ns
			$T_C = 100°C$	--	105	--	
I_{rr}	Diode Peak Reverse Recovery Current		$T_C = 25°C$	--	4.5	10	A
			$T_C = 100°C$	--	8.5	--	
Q_{rr}	Diode Reverse Recovery Charge		$T_C = 25°C$	--	112	375	nC
			$T_C = 100°C$	--	420	--	

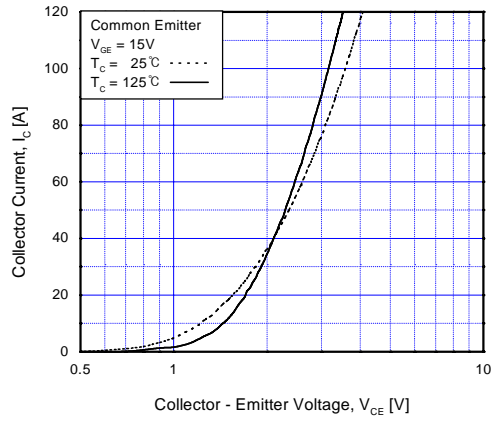Fig 1. Typical Output Characteristics

Fig 2. Typical Saturation Voltage
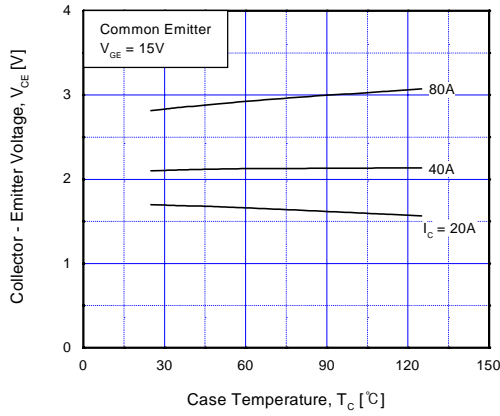Characteristics

Fig 3. Saturation Voltage vs. Case
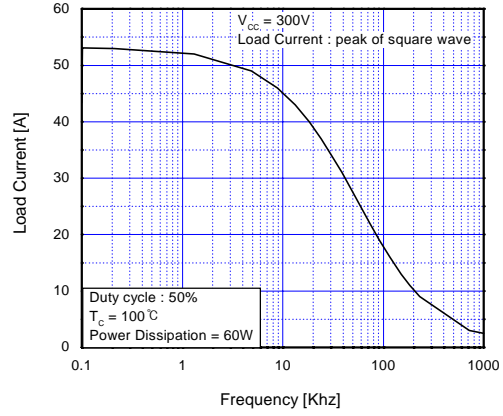Temperature at Variant Current Level
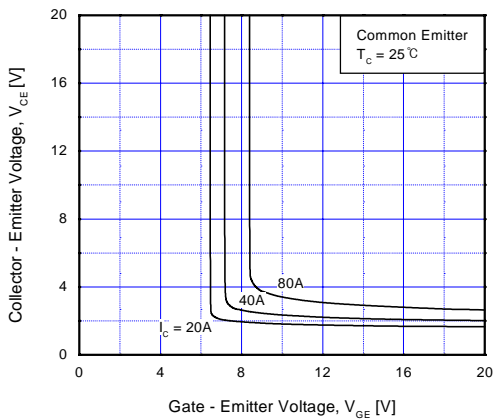

Fig 4. Load Current vs. Frequency

Fig 5. Saturation Voltage vs. V_{GE}
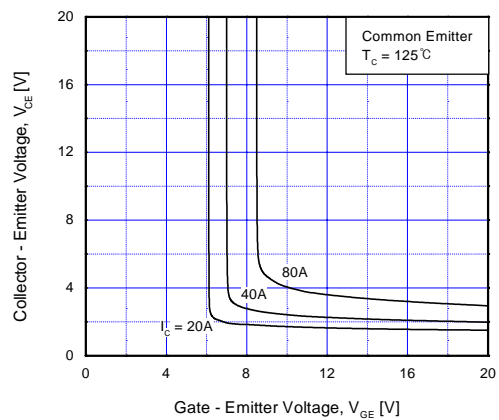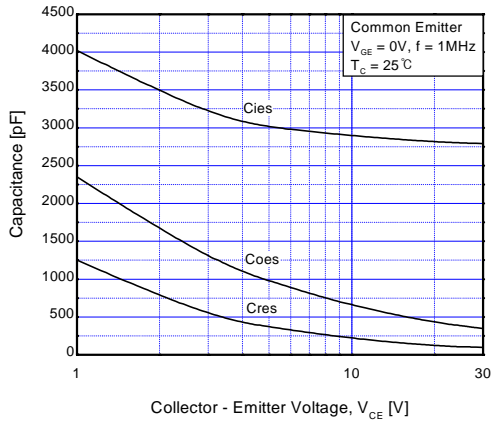

Fig 6. Saturation Voltage vs. V_{GE}
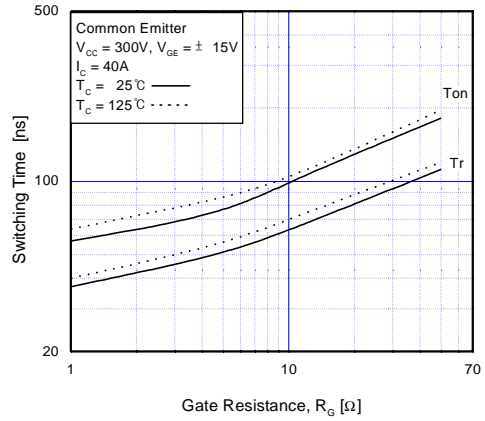
Fig 7. Capacitance Characteristics

Fig 8. Turn-On Characteristics vs. Gate Resistance

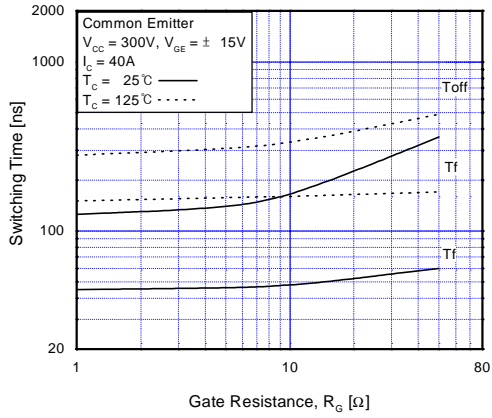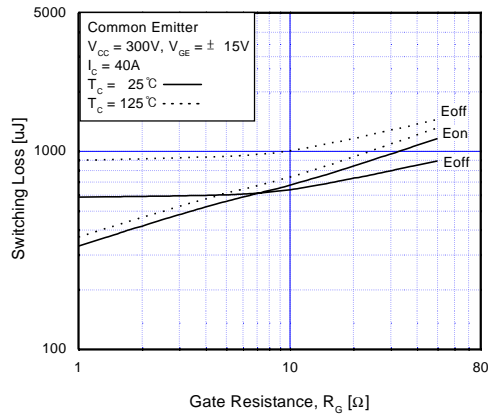**Fig 9. Turn-Off Characteristics vs. Gate Resistance**
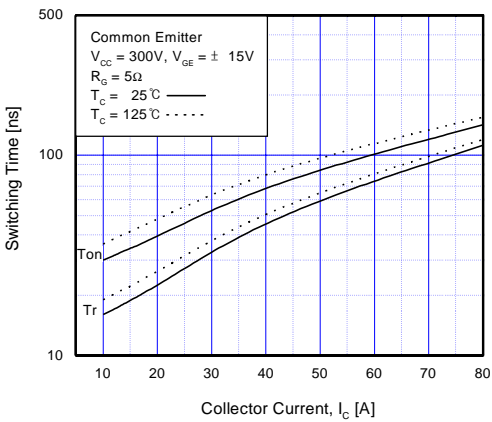
Fig 10. Switching Loss vs. Gate Resistance

Fig 11. Turn-On Characteristics vs. Collector Current
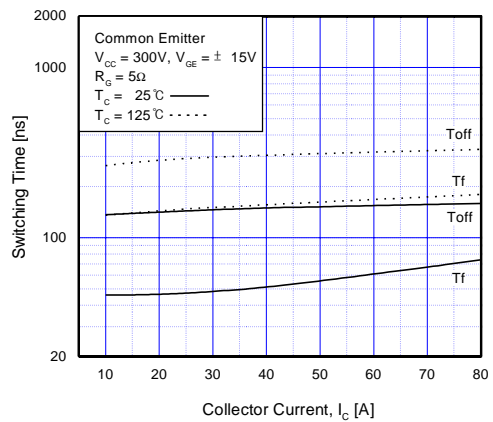
Fig 12. Turn-Off Characteristics vs. Collector Current
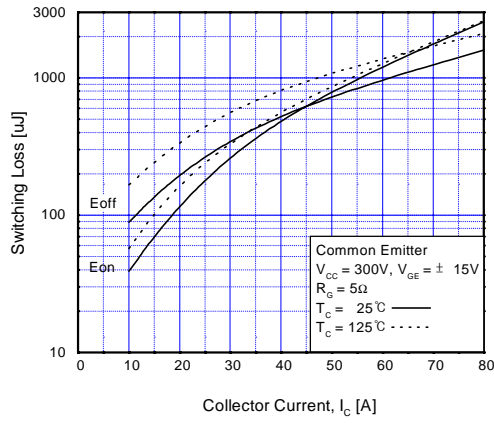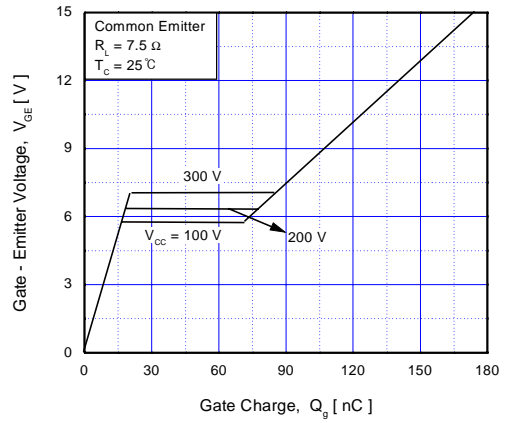
Fig 13. Switching Loss vs. Collector Current
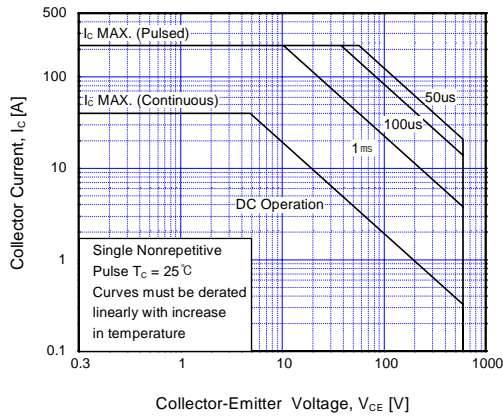
Fig 14. Gate Charge Characteristics

Fig 15. SOA Characteristics
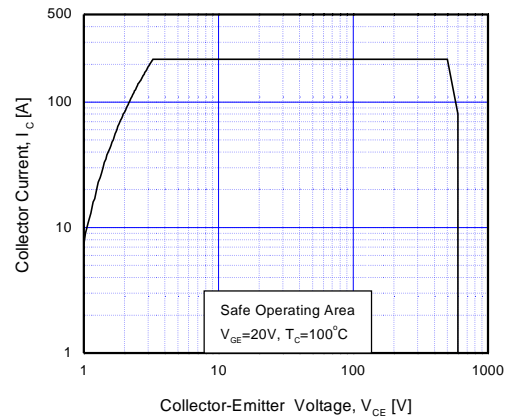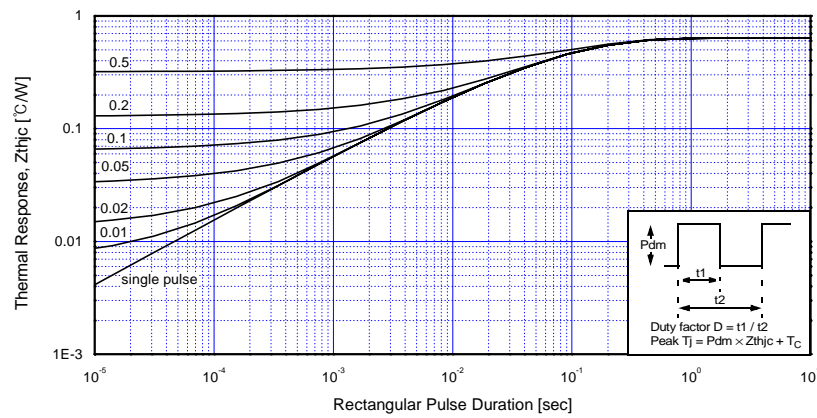
Fig 16. Turn-Off SOA Characteristics

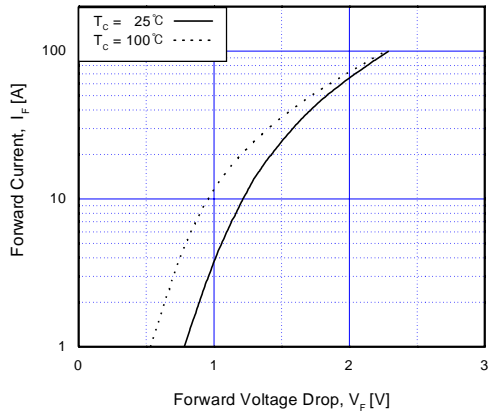**Fig 17. Transient Thermal Impedance of IGBT**
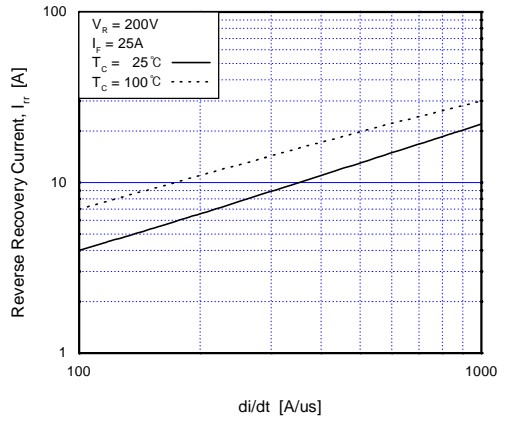
Fig 18. Forward Characteristics

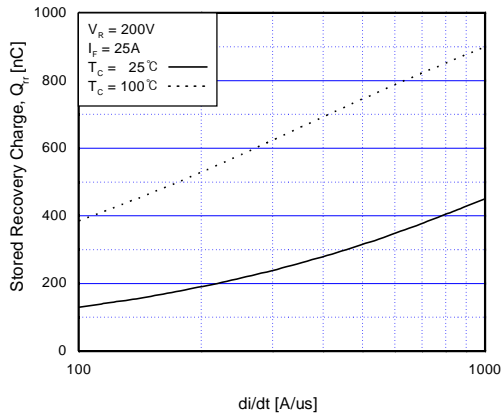**Fig 19. Reverse Recovery Current**
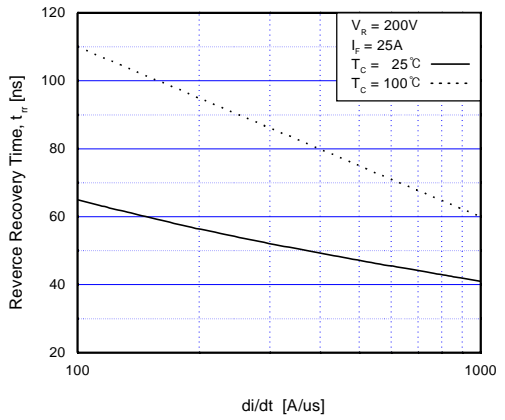

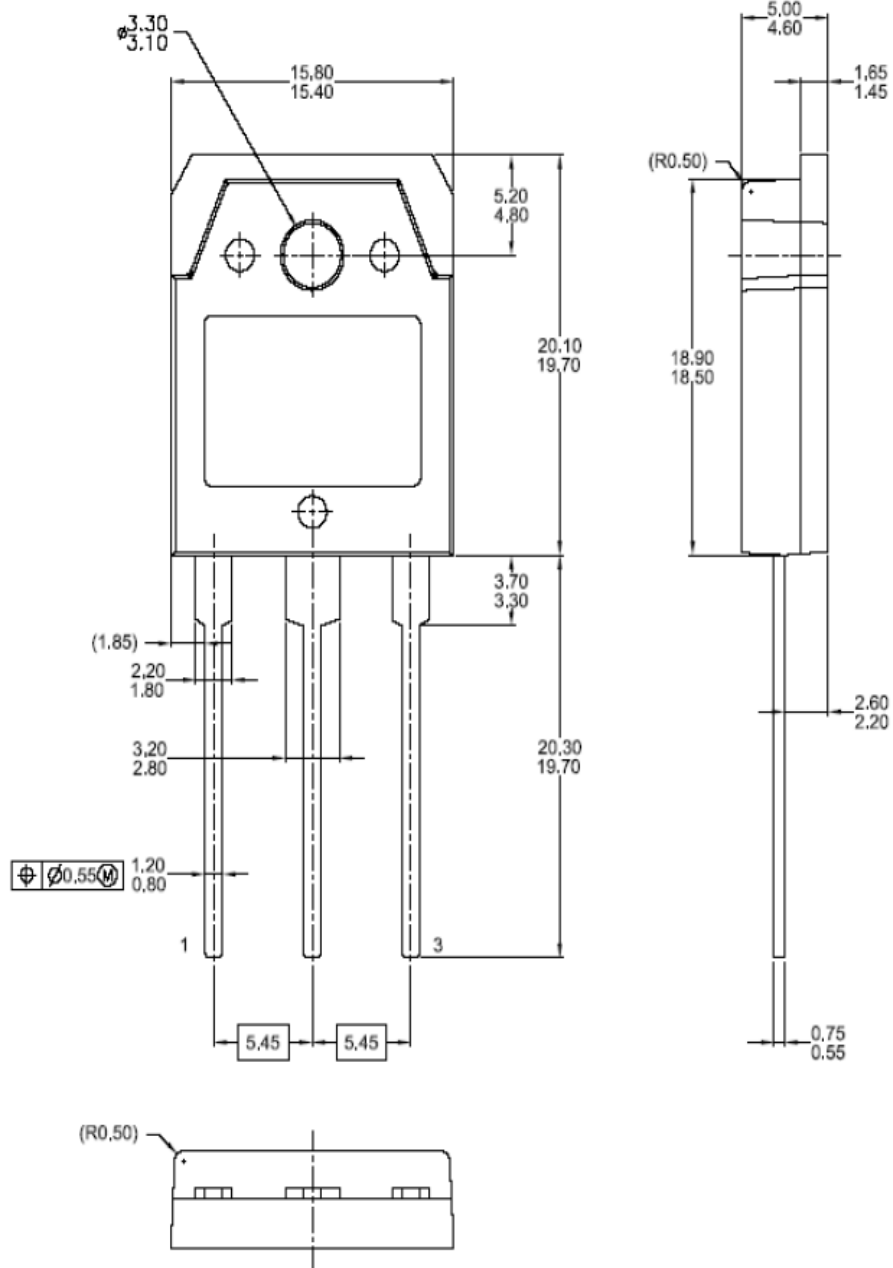**Fig 20. Stored Charge**

Fig 21. Reverse Recovery Time

Mechanical Dimensions

TO-3PN

Dimensions in Millimeters

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